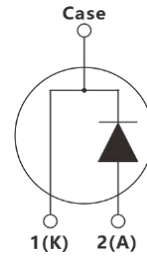


**Silicon Carbide Schottky Diode**

Parameter	Value	Unit
$V_{RRM}$	650	V
$I_F$	6	A
$Q_C$	25	nC



TO-220F-2L

**Features**

- Zero reverse recovery current
- Zero forward recovery voltage
- Temperature independent switching behavior
- High temperature operation
- High frequency operation

**Applications**

- Switched-Mode Power Supply
- Power Factor Correction
- Uninterruptible Power Supply
- Boost Converter

**Maximum Ratings** (at  $T_J=25^\circ\text{C}$  unless otherwise specified)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	$V_{RRM}$	650	V
Surge Peak Reverse Voltage	$V_{RSM}$	650	V
DC Peak Reverse Voltage	$V_R$	650	V
Continuous Forward Current $T_C = 25^\circ\text{C}$ $T_C = 135^\circ\text{C}$ $T_C = 160^\circ\text{C}$	$I_F$	18 8 6	A
Non-Repetitive Forward Surge Current $T_C = 25^\circ\text{C}, t_p = 8.3\text{ms}, \text{Half Sine Pulse}$ $T_C = 110^\circ\text{C}, t_p = 8.3\text{ms}, \text{Half Sine Pulse}$	$I_{FSM}$	60 32	A
Non-Repetitive Forward Surge Current $T_C = 25^\circ\text{C}, t_p = 8.3\text{ms}, \text{Half Sine Pulse}$ $T_C = 110^\circ\text{C}, t_p = 8.3\text{ms}, \text{Half Sine Pulse}$	$\int i^2 dt$	14.95 4.25	A <sup>2</sup> s
Power dissipation $T_C = 25^\circ\text{C}$ $T_C = 110^\circ\text{C}$	$P_{tot}$	65.2 30	W
Operating junction Range	$T_j$	-55 to +175	$^\circ\text{C}$
Storage temperature Range	$T_{stg}$	-55 to +150	$^\circ\text{C}$

**Thermal Characteristics**

Parameter	Symbol	Typ.	Unit
Thermal resistance, junction – case.	$R_{thJC}$	2.30	$^{\circ}C/W$

**Electrical Characteristics**(at  $T_J=25^{\circ}C$  unless otherwise specified)

Parameter	Symbol	Test conditions	Value			Unit
			Min.	Typ.	Max.	
DC blocking voltage	$V_{DC}$	$T_J=25^{\circ}C$	650			V
Diode forward voltage	$V_F$	$I_F=6A$ $T_J=25^{\circ}C$ $I_F=6A$ $T_J=135^{\circ}C$ $I_F=6A$ $T_J=175^{\circ}C$		1.21 1.32 1.38	1.48 1.74 1.90	V
Reverse current	$I_R$	$V_R=650V$ $T_J=25^{\circ}C$ $V_R=650V$ $T_J=175^{\circ}C$		0.5 15	50 200	$\mu A$
Total capacitive charge	$Q_C$	$V_R=400V$ $T_J=25^{\circ}C$ $Q_C = \int_0^{V_R} C(V)dV$		25		nC
Total capacitance	C	$V_R=1V$ $f=1MHz$ $V_R=300V$ $f=1MHz$ $V_R=600V$ $f=1MHz$		350 42 36		pF
Capacitance stored energy	$E_C$	$V_R=400V$		3.8		$\mu J$

**Typical Characteristics**

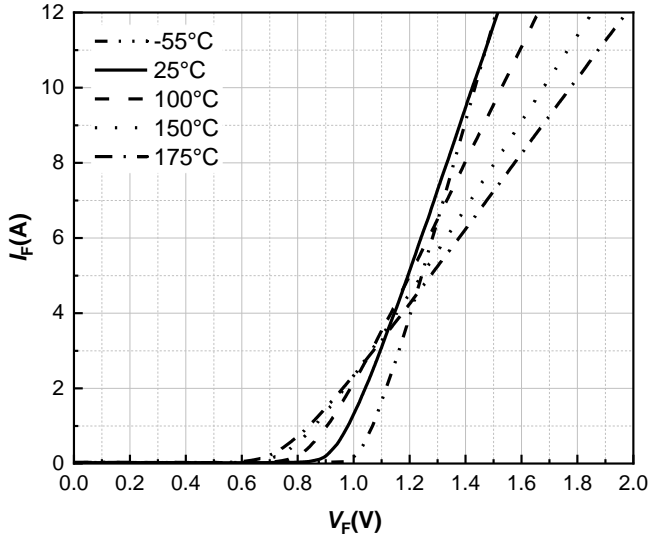


Fig 1. Typical forward characteristics

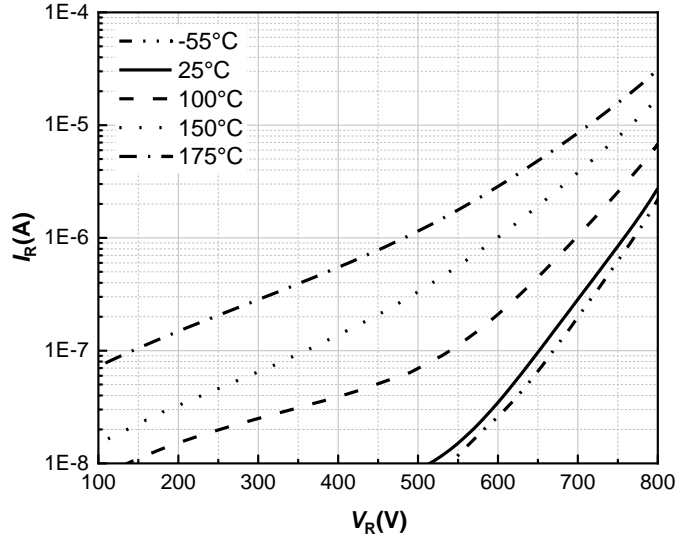


Fig 2. Typical reverse current as function of reverse voltage

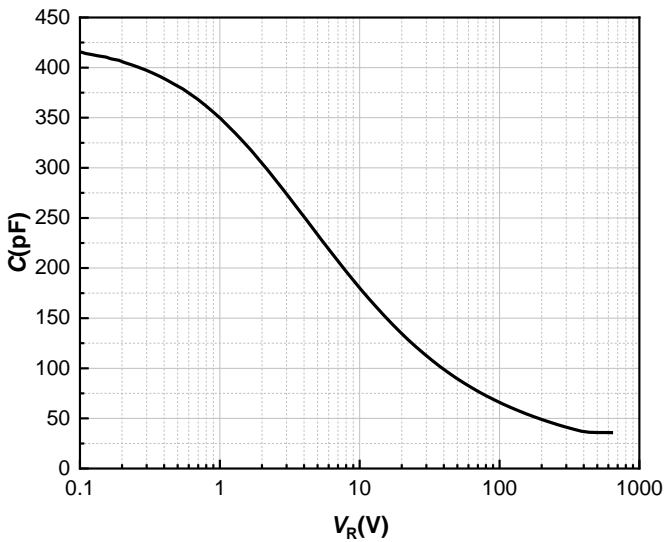


Fig 3. Typical capacitance as function of reverse voltage,  $C=f(V_R)$ ;  $T_j=25^\circ\text{C}$ ;  $f=1\text{ MHz}$

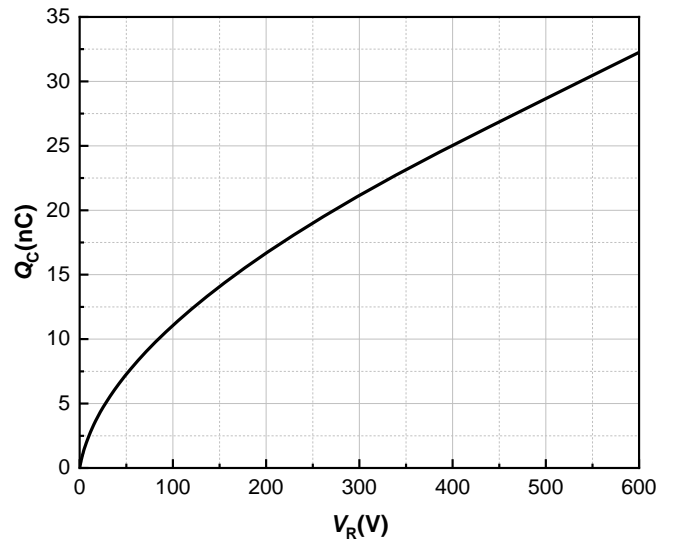
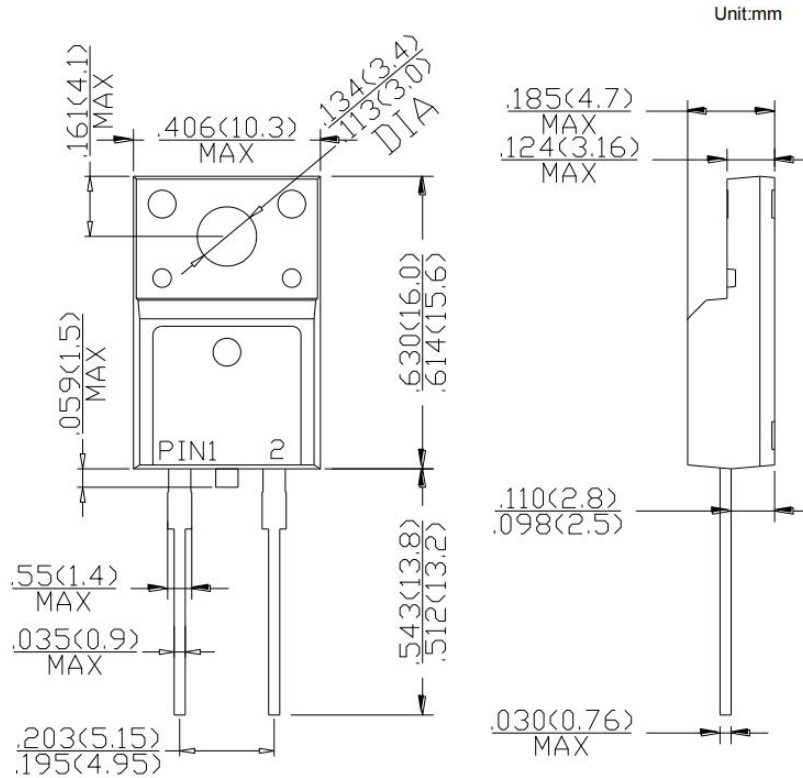


Fig 4. Typical reverse charge as function of reverse voltage

**Package Outlines(Unit:mm)**

**TO-220F-2L**



**\*Important Usage Information and Disclaimer**

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